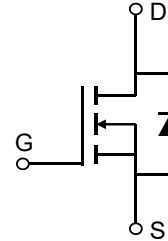


Description

Features

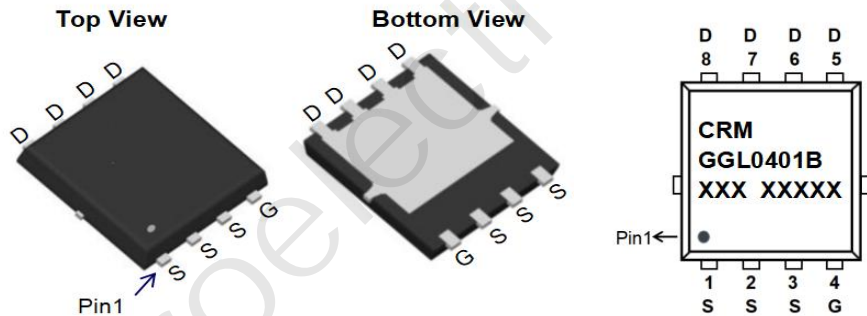
- 40V, 315A
- $R_{DS(ON)}$ Typ = 0.57mΩ @ $V_{GS} = 10V$
- $R_{DS(ON)}$ Typ = 0.79mΩ @ $V_{GS} = 4.5V$
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED!
- 100% ΔV_{ds} TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMGGL0401B	CRMGGL0401B	PDFN5x6-8L	TAPING	13"	5000	60000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units	
V _{DS}	Drain-to-Source Voltage	40	V	
V _{GS}	Gate-to-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _C = 25°C	315	A
		T _C = 100°C	189	A
I _{DM}	Pulsed Drain Current ⁽¹⁾	1260	A	
E _{AS}	Single Pulsed Avalanche Energy ⁽²⁾	689	mJ	
P _D	Power Dissipation	T _C = 25°C	125	W
R _{θJC}	Thermal Resistance, Junction to Case	1	°C/W	
T _J , T _{STG}	Junction & Storage Temperature Range	-55 to 150	°C	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	1	1.5	2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 10\text{V}$, $I_D = 30\text{A}$	-	0.57	0.74	mΩ
		$V_{GS} = 4.5\text{V}$, $I_D = 20\text{A}$	-	0.79	1.03	mΩ

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 20\text{V}$, $f = 1\text{MHz}$	-	6937	-	pF
C_{oss}	Output Capacitance		-	2427	-	pF
C_{rss}	Reverse Transfer Capacitance		-	264	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 20\text{V}$, $I_D = 20\text{A}$	-	101	-	nC
Q_{gs}	Gate Source Charge		-	25	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	22	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}$, $V_{DD} = 20\text{V}$ $I_D = 20\text{A}$, $R_{GEN} = 3\Omega$	-	15.5	-	ns
t_r	Turn-On Rise Time		-	38	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	78	-	ns
t_f	Turn-Off Fall Time		-	30	-	ns

Drain-Source Diode Characteristics and Max Ratings

I_S	Maximum Continuous Drain to Source Diode Forward Current	$V_{GS} = 0\text{V}$, $I_S = 30\text{A}$	-	-	315	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	1260	A
V_{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time		-	30	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	45	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 20\text{V}$, $V_G = 10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$, $I_{AS} = 52.5\text{A}$
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

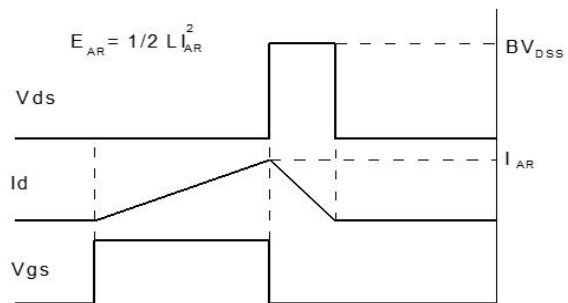
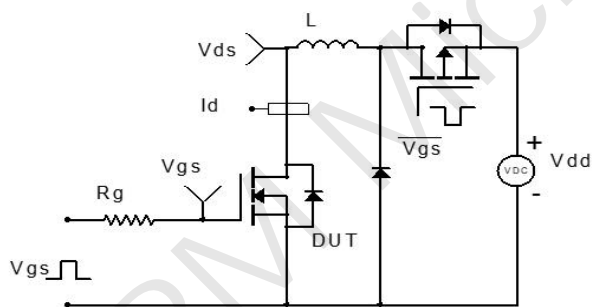


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

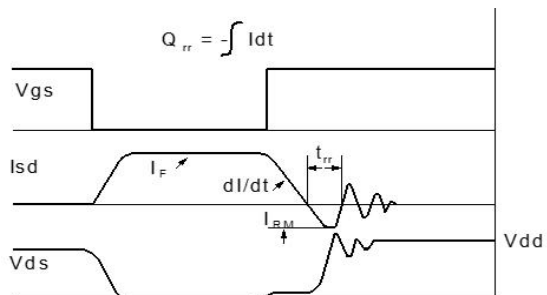
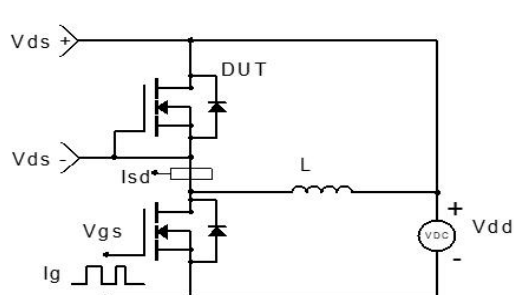
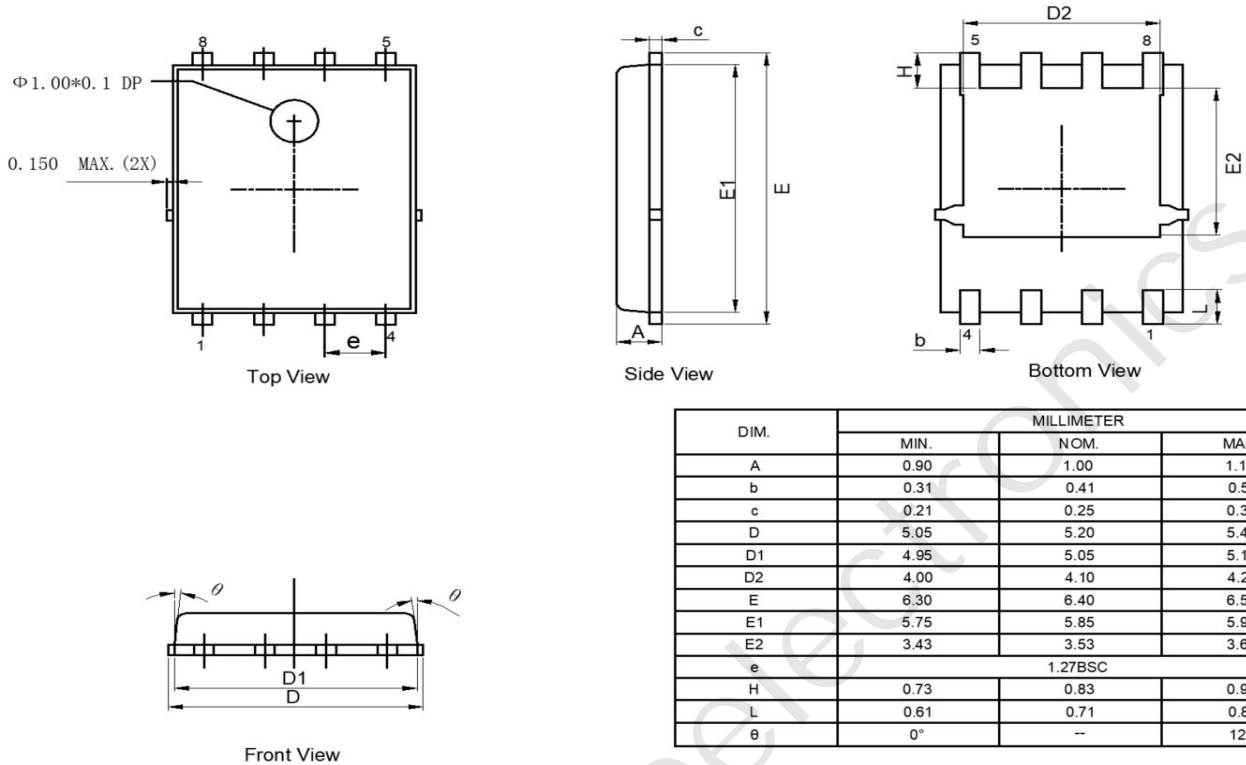


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN5x6-8L)



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